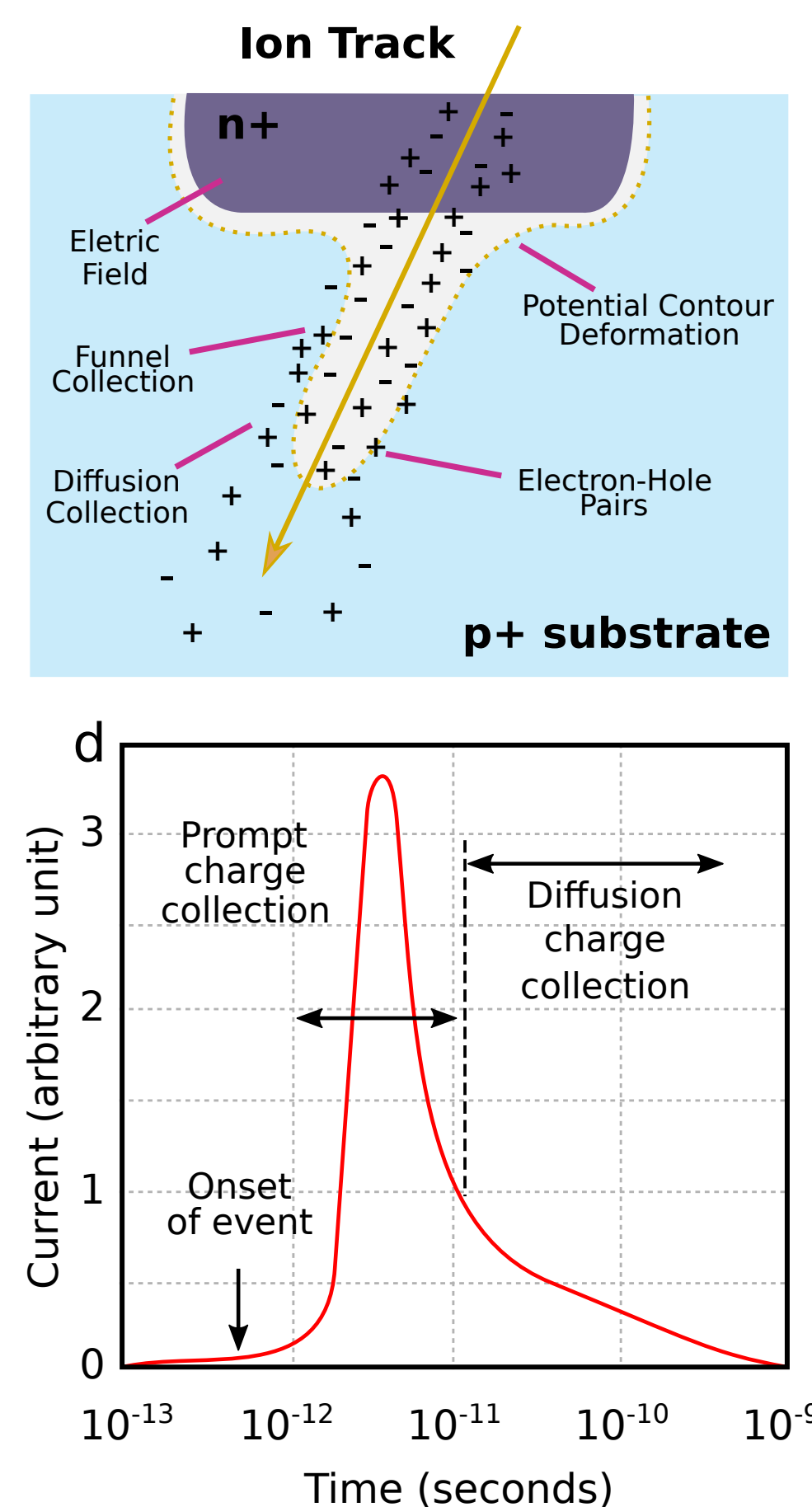
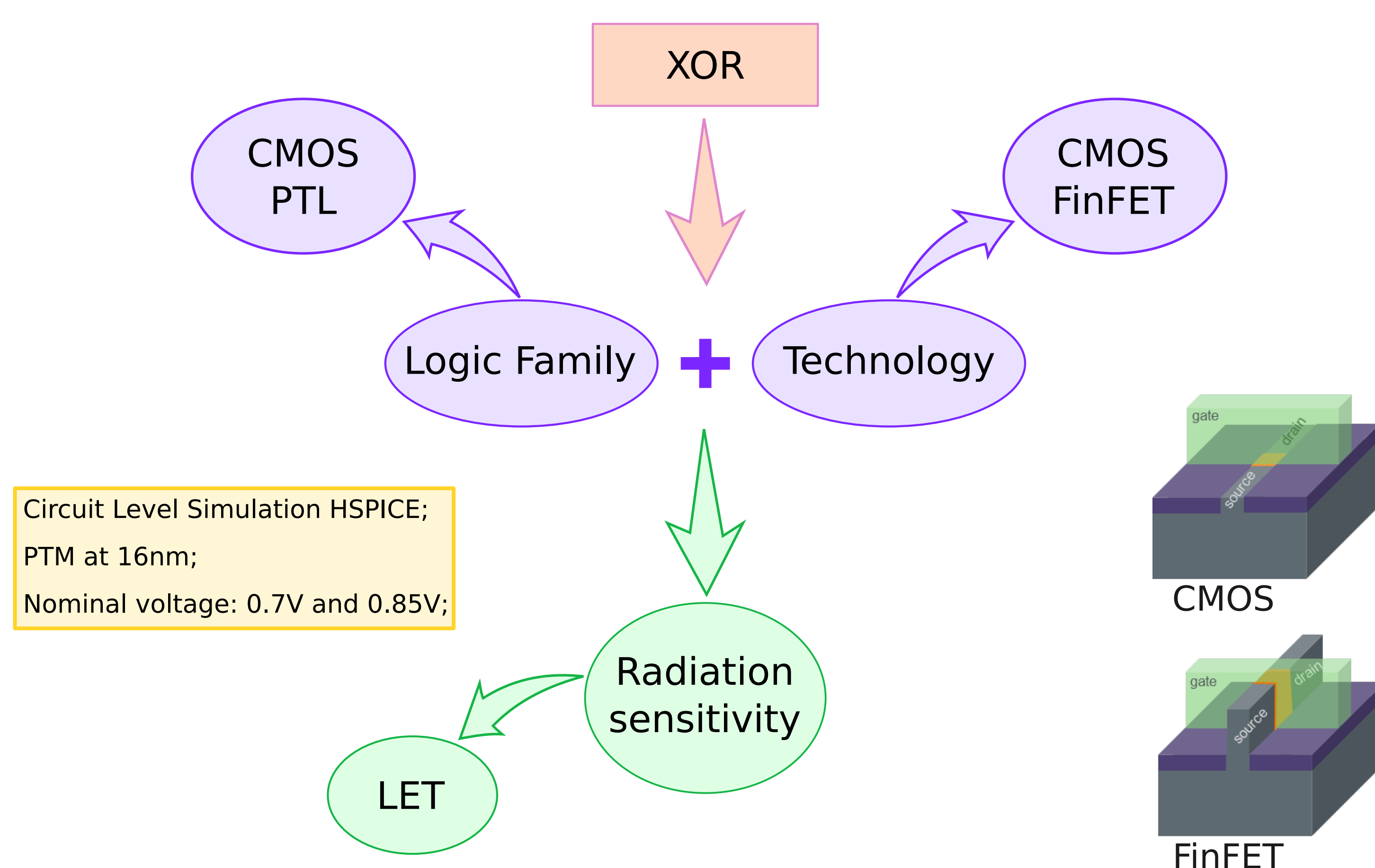


1. Introduction

- Circuits are becoming more susceptible to noise effects due to technology scaling (R. C. Baumann, IEEE T-DMR 2005).
- Particles with low energy are able to interfere within the operation of the circuits (J. Leray, RADECS 2001).
- The experiments consist of extracting minimum current that causes a fault on the device, i.e., the Linear Energy Transfer (LET) based on an analytic solution (G. C. Messenger, IEEE T NUCL SCI 1982).



2. Method



2. Topologies

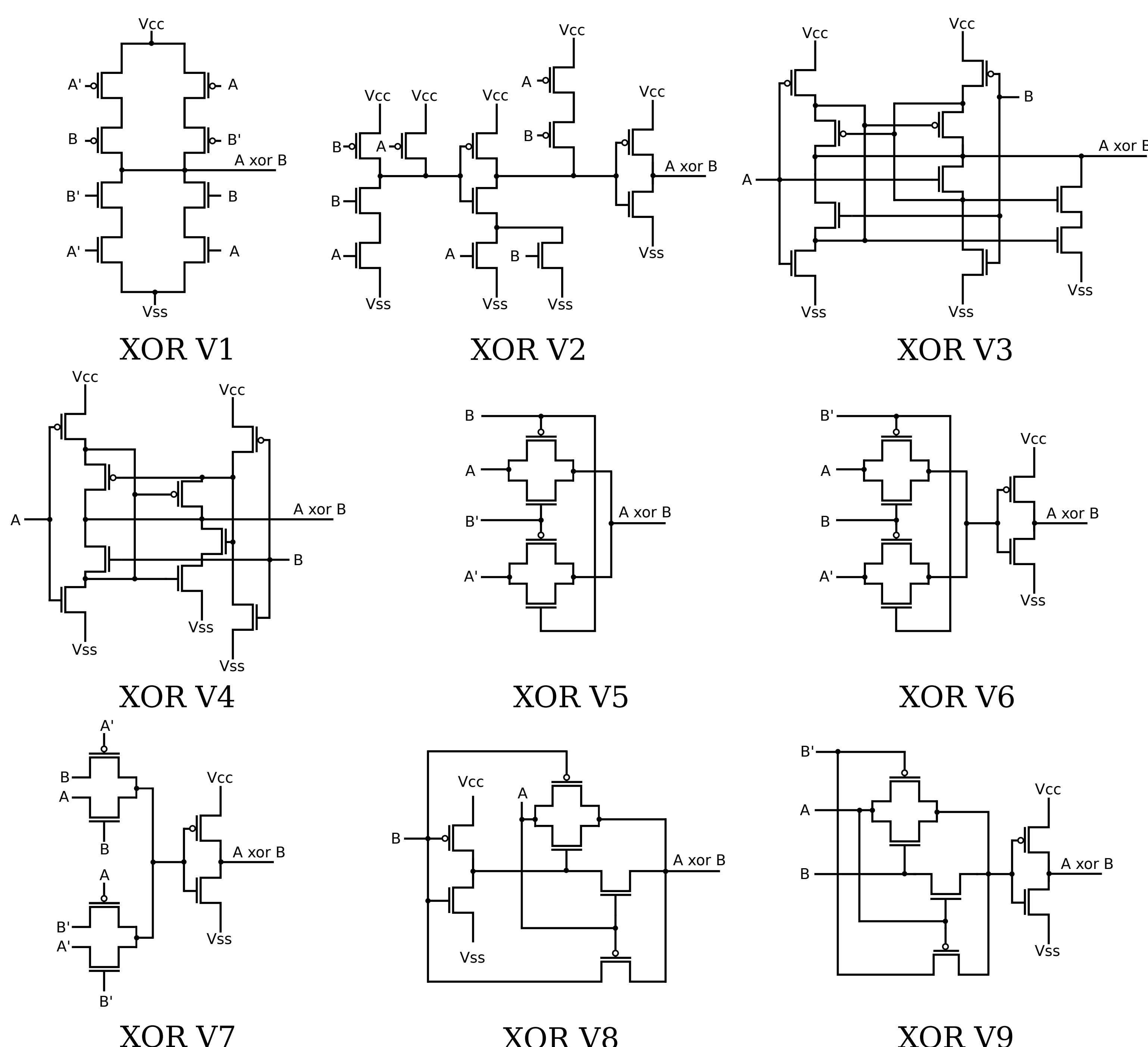
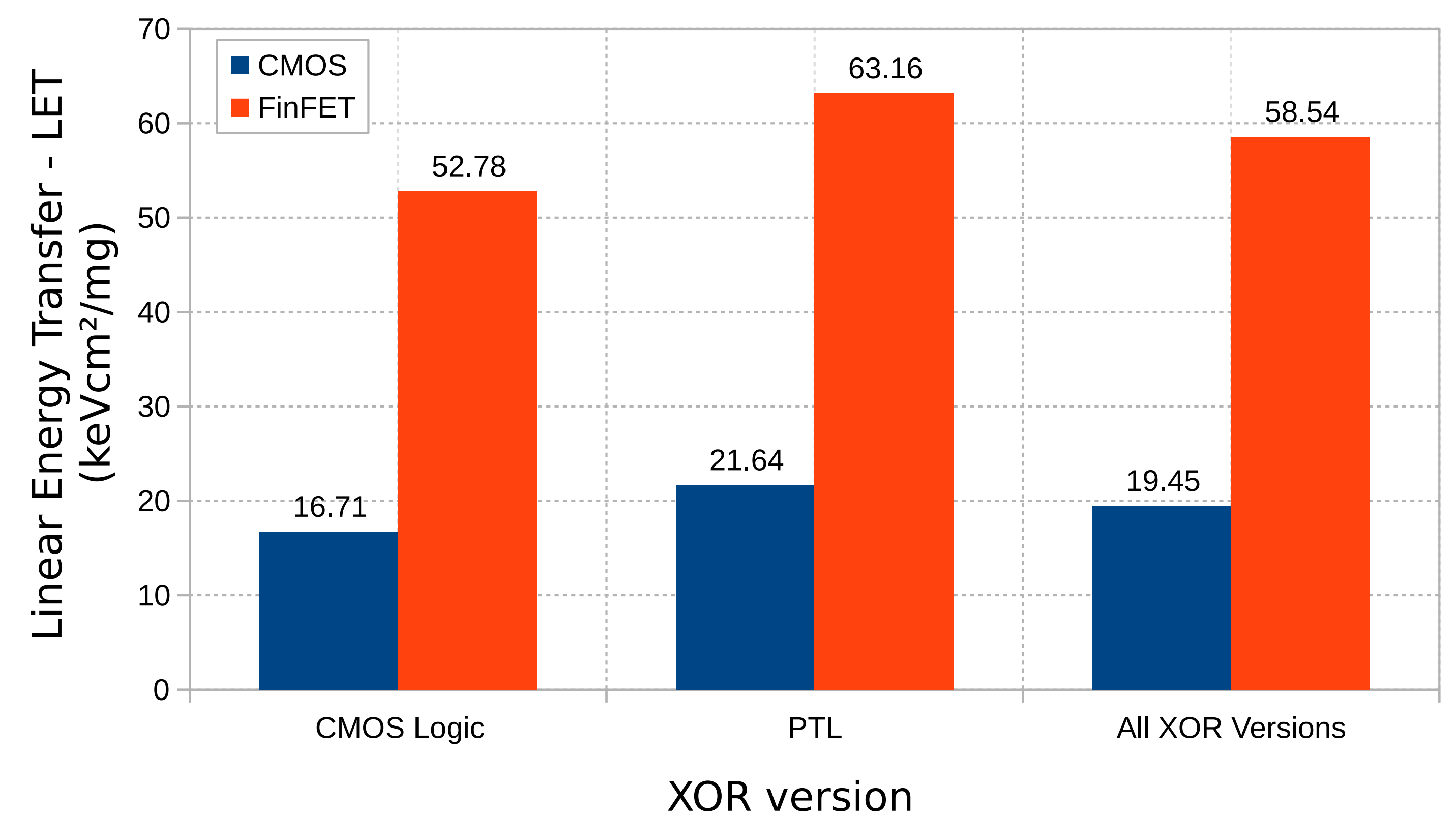


Fig. 1 XOR topologies explored in this work

4. Results

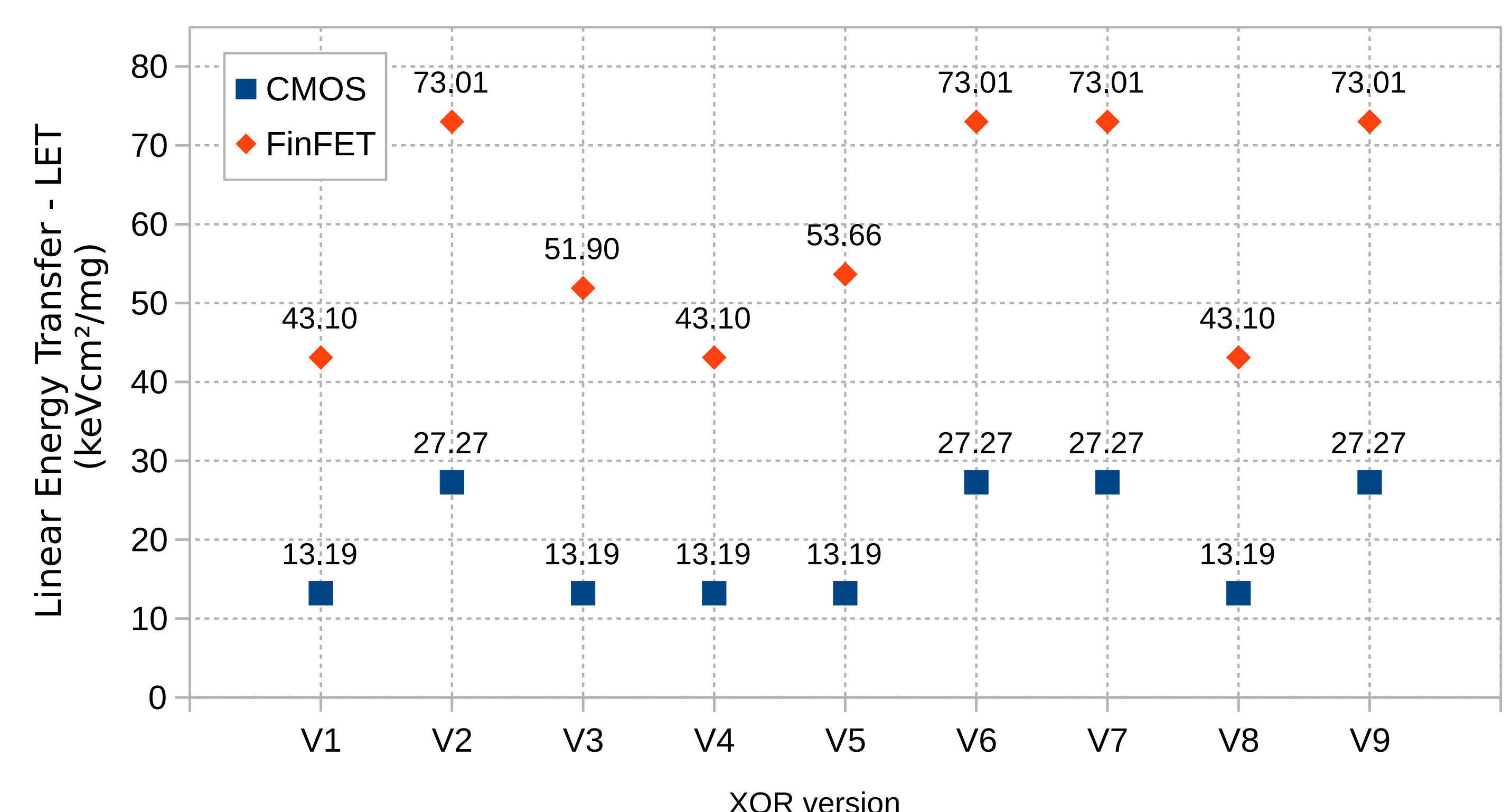
- PTL topologies had an increase in robustness up to 30% for CMOS devices and up to 20% for FinFET when compared with CMOS logic versions.
- FinFET devices improve the average robustness 2x for both logic families.



CMOS vs PTL
 ↑ **2,1x** ↑ **1,9x**
 CMOS FinFET
 Linear Energy Transfer - LET

CMOS vs FinFET
 ↑ **2x**
 FinFET
 Average LET

- For both technologies, XOR V2, V6, V7, and V9 have shown to be the least sensitive to radiation effects.
- XOR V1, one of the most common topologies found in standard cells, proved to be one of the most sensitive.
- XOR V5 implemented with FinFET technology had the greatest improvement with more than 3x when compared with its equivalent in CMOS devices.



5. Conclusion and Future Work

- This work evaluates the radiation sensitivity on 9 XOR logic gates at 16nm. PTL topologies have shown to be less sensitive against faults for both technologies analyzed. FinFET devices improve robustness up to 2x.
- As future work:
 - ➔ Investigate new methodologies to fault insertion;
 - ➔ Modeling in a new tool;
 - ➔ Transistor sizing;
 - ➔ Evaluation of different XOR topologies;

